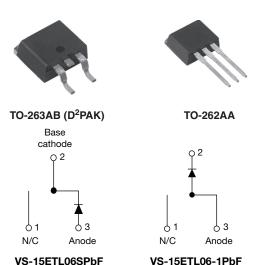


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Vishay Semiconductors

Ultralow V_F Hyperfast Rectifier for Discontinuous Mode PFC, 15 A FRED Pt®



PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	15 A
V _R	600 V
V _F at I _F	0.85 V
t _{rr} (typ.)	60 ns
T _J max.	175 °C
Diode variation	Single die

FEATURES

• Benchmark ultralow forward voltage drop



- · Hyperfast recovery time
- · Low leakage current
- 175 °C operating junction temperature

HALOGEN

FREE

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see

www.vishay.com/doc?99912

DESCRIPTION

State of the art, ultralow V_F, soft-switching hyperfast rectifiers optimized for Discontinuous (Critical) Mode (DCM) Power Factor Correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

APPLICATIONS

AC/DC SMPS 70 W to 400 W

e.g. laptop and printer AC adaptors, desktop PC, TV and monitor, games units and DVD ac-to-dc power supplies.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage	V_{RRM}		600	V		
Average rectified forward current	I _{F(AV)}	T _C = 154 °C	15			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	250	Α		
Peak repetitive forward current	I _{FM}		30			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-			
Forward voltage	V _F	I _F = 15 A	-	0.99	1.05	V		
		I _F = 15 A, T _J = 150 °C	-	0.85	0.92			
Dovoroo lookaga aurrant	,	V _R = V _R rated	-	0.1	10			
Reverse leakage current	I _R	T _J = 150 °C, V _R = V _R rated	-	15	120	μΑ		
Junction capacitance	C _T	V _R = 600 V	-	20	=	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

Revision: 20-Oct-16 Document Number: 94005



VS-15ETL06SPbF, VS-15ETL06-1PbF

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 A, dI_F/dt = 10$	00 A/μs, V _R = 30 V	-	60	120	
Boyerse receivent time		$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A}$	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		190	270	1
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	220	-	ns -
		T _J = 125 °C		-	320	-	
Dools recovery overent	I _{RRM}	T _J = 25 °C		-	19	-	^
Peak recovery current		T _J = 125 °C		-	26	-	A
Reverse recovery charge	Q _{rr}	T _J = 25 °C		=	2.2	-	μC
		T _J = 125 °C		-	4.3	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R_{thJC}		-	1.0	1.3		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased		0.5	-		
Weight			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Mayling daving		Case style TO-263AB (D2PAK)		15ETL06S			
Marking device		Case style TO-262AA	15ETL06-1				



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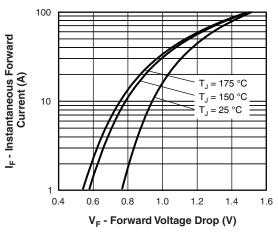


Fig. 1 - Typical Forward Voltage Drop Characteristics

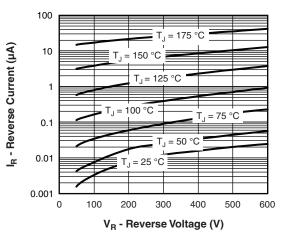


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

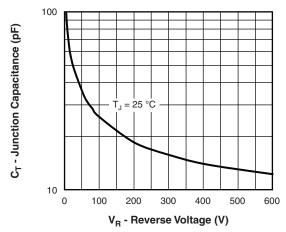


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

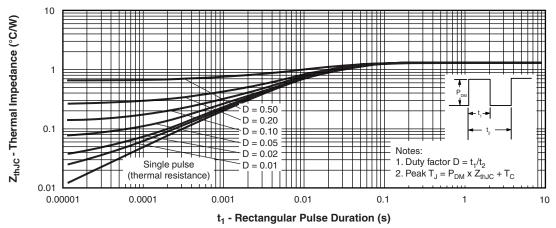


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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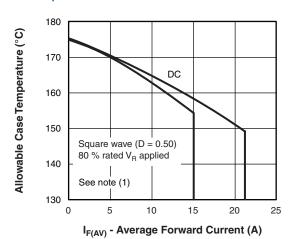


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

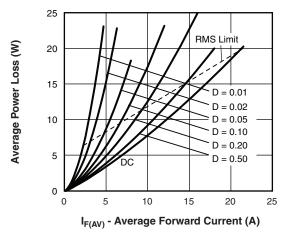


Fig. 6 - Forward Power Loss Characteristics

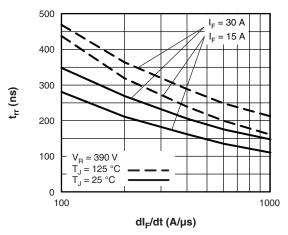


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

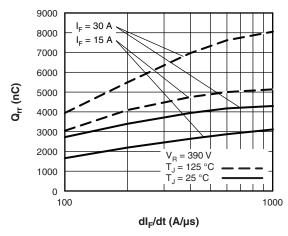


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$

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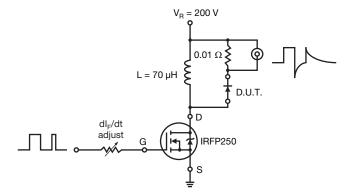
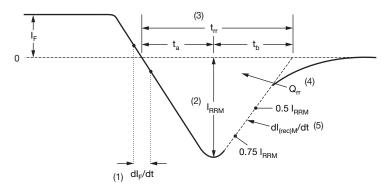


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

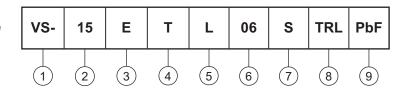


VS-15ETL06SPbF, VS-15ETL06-1PbF

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (15 A)

3 - E = single diode

- T = TO-220, D²PAK

5 - L = ultralow V_F hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - • S = D²PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - PbF = lead (Pb)-free

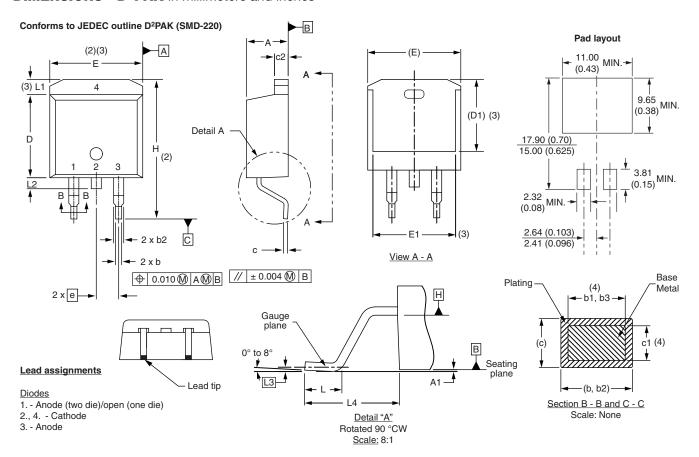
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95014					
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					
SPICE model	www.vishay.com/doc?96051					



Vishay Semiconductors

D²PAK, TO-262

DIMENSIONS - D²PAK in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIN	IETERS	INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25 BSC		0.010	BSC		
L4	4.78	5.28	0.188	0.208		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

(7) Outline conforms to JEDEC outline TO-263AB

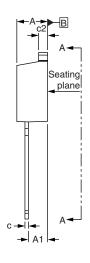
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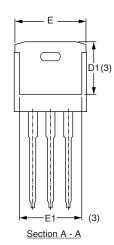
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D²PAK, TO-262



DIMENSIONS - TO-262 in millimeters and inches





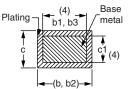
⊕ 0.010 A B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	ETERS	INC	INCHES		
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

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